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1. (Once Amended) A contact structure for an integrated circuit comprising:  
a lower bulk insulator layer situated above a semiconductor substrate;  
a conductor layer situated above the lower bulk insulator layer;  
a sleeve insulator layer in contact with the conductor layer; and  
a conductor structure extending from and beyond the sleeve insulator layer to  
terminate at a contact on said semiconductor substrate, said conductor structure being  
electrically insulated from the conductor layer by the sleeve insulator layer.

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13. (Once Amended) A contact structure for an integrated circuit comprising:  
a lower bulk insulator layer situated above a semiconductor substrate;  
a conductor layer situated above the lower bulk insulator layer;  
an upper bulk insulator layer upon the conductor layer, said upper bulk insulator layer  
having sidewall;  
a sleeve insulator layer in contact with the conductor layer, wherein the sidewall of  
the upper bulk insulator layer is in contact with the sleeve insulator layer; and  
a conductive plug extending from and beyond the sleeve insulator layer to terminate  
at a contact on said semiconductor substrate, said conductive plug being electrically insulated  
from the conductor layer by the sleeve insulator layer.

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15. (Once Amended) A contact structure for an integrated circuit comprising:

- a lower bulk insulator layer situated above a semiconductor substrate;
- a dielectric layer situated above the lower bulk insulator layer;
- a conductor layer situated above the lower bulk insulator layer and above the dielectric layer;
- an electrically insulating layer situated upon the conductor layer;
- a sleeve insulator layer in contact with the conductor layer and extending from the conductor layer to terminate within the lower bulk insulator layer above the semiconductor substrate, said sleeve insulator layer extending through and being in contact with each of the lower bulk insulator layer and the conductor layer, wherein each of the lower bulk insulator layer and the conductor layer has a sidewall in contact with the sleeve insulator layer; and
- a conductive plug extending from and beyond the sleeve insulator layer to terminate at a contact on said semiconductor substrate, said conductive plug being electrically insulated from the conductor layer by the sleeve insulator layer.

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19. (Once Amended) A contact structure for an integrated circuit comprising:
- a semiconductor substrate having an active region therein;
  - a capacitor storage node in contact [in electrical communication] with the active region;
  - a capacitor dielectric upon the capacitor storage node;
  - a capacitor cell plate upon the capacitor dielectric;
  - an electrically conductive plug in contact with the active region and the storage node;
  - a first dielectric layer insulating the capacitor cell plate from the electrically conductive plug, the electrically conductive plug projecting from the active region above the first dielectric layer and the capacitor cell plate.

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22. (Once Amended) A contact structure for an integrated circuit comprising:
- a lower bulk insulator layer situated above a semiconductor substrate;
  - a dielectric layer above the lower bulk insulator layer;
  - a conductor layer situated above the dielectric layer;
  - [an electrically insulating layer formed conformably upon the conductor layer and having a sidewall that is in contact with the sleeve insulator layer;]
  - a sleeve insulator layer, composed of a material [selective] selected from the group consisting of  $Ta_2O_5$  and  $Si_3N_4$ , and [extending] such that the sleeve insulator layer:
    - extends through and [being] is in contact with each of the lower bulk insulator layer and the conductor layer;
    - [to] is in contact with the dielectric layer; and
    - extends from the conductor layer to terminate within the lower bulk insulator layer above the semiconductor substrate; [and]
  - an electrically insulating layer formed conformably upon the conductor layer and having a sidewall that is in contact with the sleeve insulator layer; and
  - a conductor structure terminating at a refractory metal silicide material contact on said semiconductor substrate and being electrically insulated from the conductor layer by the sleeve insulator layer.